

• FEATURES

- Drain Current: $I_D = 80A @ T_C = 25^\circ C$
- Drain Source Voltage
: $V_{DSS} = 80V(\text{Min})$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 11m\Omega (\text{Max})$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

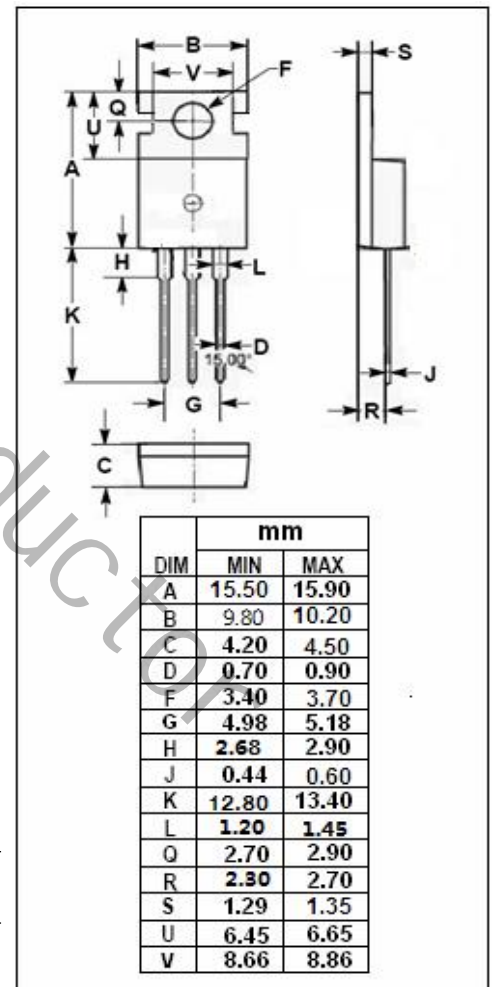
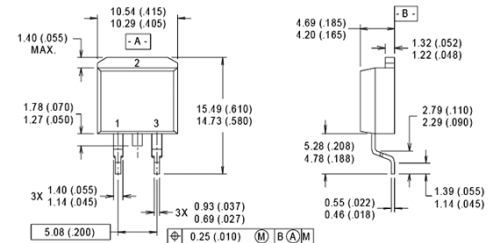
- Power switching applications
- Hard switched and high frequency circuits

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	80	A
I_{DM}	Drain Current-Single Plused	380	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	220	W
T_j	Max. Operating Junction Temperature	175	$^\circ C$
T_{stg}	Storage Temperature	-55~175	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.68	$^\circ C/W$



• ELECTRICAL CHARACTERISTICS
 $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	80			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
V_{SD}	Diode Forward On-voltage	$I_S=40\text{A}; V_{GS}=0$			1.2	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=40\text{A}$			11	$\text{m}\Omega$
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=80\text{V}; V_{GS}=0$			1	μA